

### **Description**

The AO6800-HXY uses advanced trench technology

to provide excellent R<sub>DS(ON)</sub>, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



## SOT23-6L

### **General Features**

 $V_{DS} = 30V I_{D} = 4.5 A$ 

 $R_{DS(ON)} < 38m\Omega$  @  $V_{GS}=10 V$ 

## **Application**

Battery protection

Load switch

Uninterruptible power supply





**Dual N-Channel MOSFET** 

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
AO6800-HXY	SOT23-6L	6800 XXX YYYY	3000

## Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	<u>+</u> 12	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	4.5	Α
Ірм	Pulsed Drain Current <sup>1</sup>	15	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	1.25	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient <sup>3</sup>	125	°C/W



# **Electrical Characteristics** (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Charac	Off Characteristic						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250µA	30	-	_	V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μA	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	_	±100	nA	
On Characteristics							
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V	
Б	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4A	-	29	38	mΩ	
R <sub>DS(on)</sub>		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	45	65		
Dynamic C	Characteristics		•				
C <sub>iss</sub>	Input Capacitance	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	233	_	pF	
Coss	Output Capacitance	$V_{DS}$ =15V, $V_{GS}$ =0V,	-	44	-	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	33	-	pF	
Qg	Total Gate Charge	\/ -15\/   -20	-	3	-	nC	
Qgs	Gate-Source Charge	$V_{DS}$ =15V, $I_{D}$ =2A, $V_{GS}$ =10V	-	0.5	-	nC	
$Q_{gd}$	Gate-Drain("Miller") Charge	VGS-10V	-	0.8	1	nC	
Switching	Characteristics						
t <sub>d(on)</sub>	Turn-on Delay Time	\/ 45\/	-	4	-	ns	
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =15V,	-	2.1	-	ns	
t <sub>d(off)</sub>	Turn-off Delay Time	$I_D$ =4A, $R_{GEN}$ =3 $\Omega$ , $V_{GS}$ =10V	-	15	-	ns	
t <sub>f</sub>	Turn-off Fall Time	- VGS-10V	-	3.2	-	ns	
Drain-Soul	rce Diode Characteristics and Maxim	um Ratings	•				
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	4.5	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	Α	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage  V <sub>GS</sub> =0V, I <sub>S</sub> =4A		-	-	1.2	V	

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



# **Typical Performance Characteristics**

Figure1: Output Characteristics

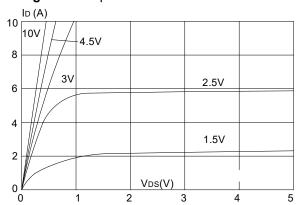


Figure 3:On-resistance vs. Drain Current

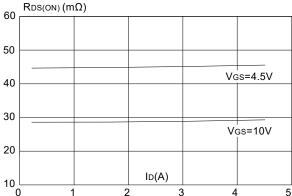


Figure 5: Gate Charge Characteristics

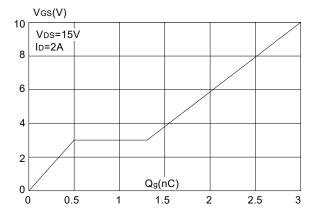


Figure 2: Typical Transfer Characteristics

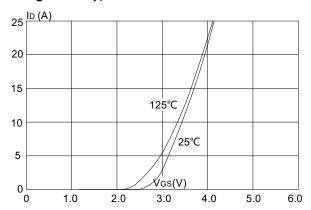


Figure 4: Body Diode Characteristics

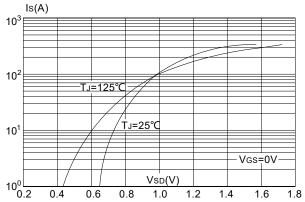
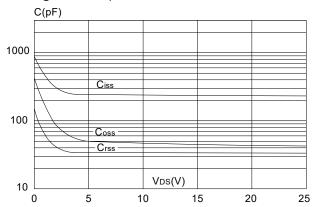


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

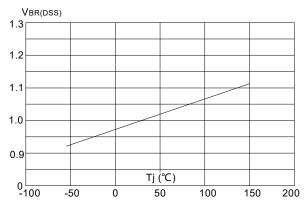
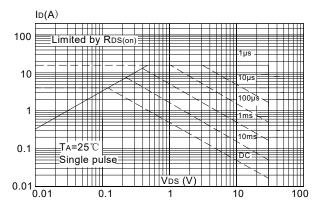
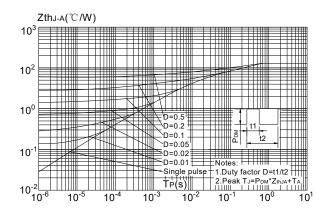


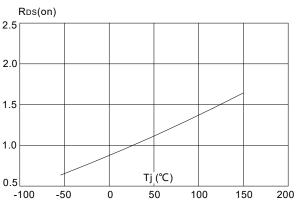
Figure 9: Maximum Safe Operating Area



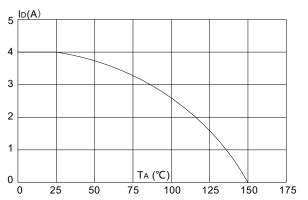
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



**Figure 8:** Normalized on Resistance vs. Junction Temperature

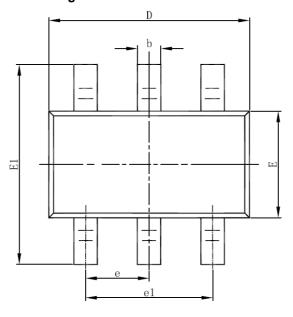


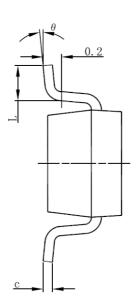
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

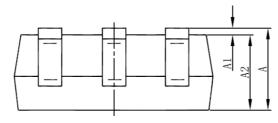




## **SOT23-6L Package Information**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

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